

L Number	Hits	Search Text	DB	Time stamp
-	71	356/\$.ccls. and (gate adj oxide)	USPAT; US-PGPUB; EPO; JPO; DEPWENT; IEM_TDB	2003/07/02 14:04
-	59	356/\$.ccls. and (gate adj oxide)	USPAT	2003/07/02 14:05
-	5	(gate adj oxide) and thickness and (high\$lk) and scatter\$	USPAT	2003/07/02 15:19
-	55	356/\$.ccls. and (gate adj oxide) and thickness	USPAT; US-PGPUB; EPO; JPO; DEPWENT; IBM_TDB	2003/07/02 15:25
-	231	hallyal-arvind singh-bhanwar subramanian-ramkumar).in.	USPAT; US-PGPUB; EPO; JPO; DEPWENT; IBM_TDB	2003/07/02 15:26
-	18	hallyal-arvind singh-bhanwar subramanian-ramkumar).in. and (gate adj oxide) and thickness	USPAT; US-PGPUB; EPO; JPO; DEPWENT; IBM_TDB	2003/07/02 15:26
-	22	356/\$.ccls. and (gate adj oxide) and thickness or uniform\$) and scatter\$	USPAT	2003/07/06 14:44
-	28	356/\$.ccls. and (gate adj oxide) and thickness or uniform\$) and scatter\$	USPAT; US-PGPUB; EPO; JPO; DEPWENT; IBM_TDB	2003/07/06 16:56
-	9	:"4710030" "4750812" "5298970" "5603526" "5798837" "5976074" "6060374" "6081330" "6361009").PN.	USPAT	2003/07/06 16:58
-	5	:"4710030" "4750812" "5298970" "5603526" "5798837" "5976074" "6060374" "6081330" "6361009").PN. and scatter\$	USPAT	2003/07/06 16:59
-	0	:"4710030" "4750812" "5198970" "5603526" "5798837" "5976074" "6060374" "6081330" "6361009").PN. and scatter\$ and (gate adj oxide)	USPAT	2003/07/06 16:59
-	32	356/\$.ccls. and (gate adj oxide) and thickness or uniform\$) and scatter\$	USPAT	2003/07/06 16:30
-	30	356/\$.ccls. and (gate adj oxide) and thickness or uniform\$) and scatter\$ not 356/\$.ccls.	USPAT	2003/07/06 16:30
-	33	356/\$.ccls. and (gate adj oxide) and (thickness or uniform\$) and scatter\$ not 356 \$.ccls.	USPAT; US-PGPUB; EPO; JPO; DEPWENT; IBM_TDB	2003/07/06 16:45
-	622	((gate adj oxide) with (thickness or uniform\$)) and scatter\$	USPAT; US-PGPUB; EPO; JPO; DEPWENT; IBM_TDB	2003/07/09 12:10
-	19	((gate adj oxide) with (thickness or uniform\$)) and scatter\$.clm.	USPAT; US-PGPUB; EPO; JPO; DEPWENT; IBM_TDB	2003/07/09 16:46
-	2	356/63]-632.ccls. and (gate adj oxide) and scatter\$	USPAT; US-PGPUB; EPO; JPO; DEPWENT; IEM_TDB	2003/07/09 16:26
-	14	((gate adj oxide) with (thickness or uniform\$)).ab. and scatter\$	USPAT; US-PGPUB; EPO; JPO; DEPWENT; IBM_TDB	2003/07/09 12:38

0	("5862054" "6060374" "5880040").pn. and scatter\$	USPAT	2003/07/09 12:37
3	("5862054" "6060374" "5880040").pn.	USPAT	2003/07/09 12:37
9452	438/163,786,514,14-18,769 257/e11.193,e19.162 700/111,108,109 702/181).ccls. ((gate adj oxide) with thickness or uniform\$) and scatter\$ and nitrid\$ or nitrogen\$)	US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2003/07/09 12:41
9035	438/163,786,514,14-18,769 257/e11.193,e19.162 700/111,108,109 702/181).ccls. ((gate adj oxide) with thickness or uniform\$) and scatter\$.ab. and nitrid\$ or nitrogen\$	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2003/07/09 12:41
4	438/163,786,514,14-18,769 257/e11.193,e19.162 700/111,108,109 702/181).ccls. and ((gate adj oxide) with thickness or uniform\$) and scatter\$.ab. and nitrid\$ or nitrogen\$	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2003/07/09 12:44
1	438/163,786,514,14-18,769 257/e11.193,e19.162 700/111,108,109 702/181).ccls. and ((gate adj oxide) with thickness or uniform\$).ab. and scatter\$ and nitrid\$ or nitrogen\$	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2003/07/09 12:45
31	438/163,786,514,14-18,769 257/e11.193,e19.162 700/111,108,109 702/181).ccls. and ((gate adj oxide) with thickness or uniform\$) and scatter\$ and nitrid\$ or nitrogen\$	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2003/07/10 15:43
3	("6526433" "5904523" "6060374").pn.	USPAT	2003/07/09 15:13
2	("20020023900" "20030042412").pn.	USPAT	2003/07/09 15:13
116	356/630-631.ccls. and (semiconductor or wafer) and scatter\$	US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2003/07/09 16:26
10	356/630-631.ccls. and (semiconductor or wafer) and scatter\$.ab.	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2003/07/10 11:43
1	356/630-632.ccls. and (semiconductor or wafer) and (scatterometry with thickness)	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2003/07/09 16:36
0	(scatterometry with nitrogen) and (semiconductor or wafer)	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2003/07/09 16:36
0	(scatterometry with nitrogen)	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2003/07/09 16:36
679	scatter\$ with nitrogen)	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2003/07/09 16:36
195	scatter\$ with nitrogen) and semiconductor or wafer or (gate adj oxide)	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2003/07/09 16:37
55	scatter\$ with nitrogen) and semiconductor or wafer or (gate adj oxide) and scatter\$.ab.	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2003/07/09 16:39

47	(scatter\$ with nitrogen) and (semiconductor or wafer or (gate adj oxide) and scatter\$.ab. not (electron near4 beam)	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM TDB	2003/07/09 16:40
26	scatter\$ with nitrogen) and semiconductor or wafer or gate adj oxide) and (scatter\$ and (nitrogen or nitride\$).ab. not (electron near4 beam)	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM TDB	2003/07/09 16:40
9	"5867276" "5877850" "5880833" "6081348" "6081334" "6141107" "6245564" "6383886" "6423977").PN.	USPAT	2003/07/10 11:16
1	"5867276" "5877850" "5880833" "6081348" "6081334" "6141107" "6145564" "6383886" "6423977").PN. and scatter\$.ab.	USPAT	2003/07/10 11:18
4	"4710642" "5164730" "5241369" "5703692").PN.	USPAT	2003/07/10 11:17
4	"5867276" "5877850" "5880833" "6081348" "6081334" "6141107" "6245564" "6383886" "6423977").PN. and scatterom\$	USPAT	2003/07/10 11:18
17	356/630-631.ccls. and (sem conductor or wafer) and scatterom\$	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM TDB	2003/07/10 12:01
16	356/630(-631.ccls. and (semiconductor or wafer) and scatterom\$ not scatter\$.ab.	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM TDB	2003/07/10 12:43
6	356/230.4,137.5.ccls. and (semiconductor or wafer) and scatterom\$ and thickness	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM TDB	2003/07/10 14:17
7	250/554.27.ccls. and (semiconductor or wafer) and scatterom\$	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM TDB	2003/07/10 11:55
1	250/554.27.ccls. and (semiconductor or wafer) and scatterom\$	USPAT; EPO; JPO; DEFWENT; IBM TDB	2003/07/10 11:55
21	356/630-631.ccls. and scatterom\$	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM TDB	2003/07/10 12:01
10	356/630-631.ccls. and scatterom\$	USPAT	2003/07/10 12:01
154	356/630-631.ccls. and scatter\$	USPAT	2003/07/10 12:01
20	356/630-632.ccls. and scatter\$.ab.	USPAT	2003/07/10 12:02
20	356/630-632.ccls. and scatter\$.ab. and scatter\$	USPAT	2003/07/10 12:02
35	356 \$.ccls. and (semiconductor or wafer) and scatterom\$.ab.	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM TDB	2003/07/10 14:17
8	("i393624" "5867276" "5923423" "610095" "6259521" "6266125" "6746253" "6424417").PN.	USPAT	2003/07/10 15:27
2	("i393624" "5867276" "5923423" "610095" "6259521" "6266125" "6746253" "6424417").PN. and (nitrogen\$ or nitride\$)	USPAT	2003/07/10 15:27

	61	(438/263,736,514,14-18,769 257,e21.193,e29.162 700/121,108,109 702/181).ccls. and ((gate adj oxide) with cvd;	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/10 15:54
	19	(438/263,736,514,14-18,769 257,e21.193,e29.162 700/121,108,109 702/181).ccls. and (gate adj oxide).ab. and ((gate adj oxide) with cvd)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/10 15:57